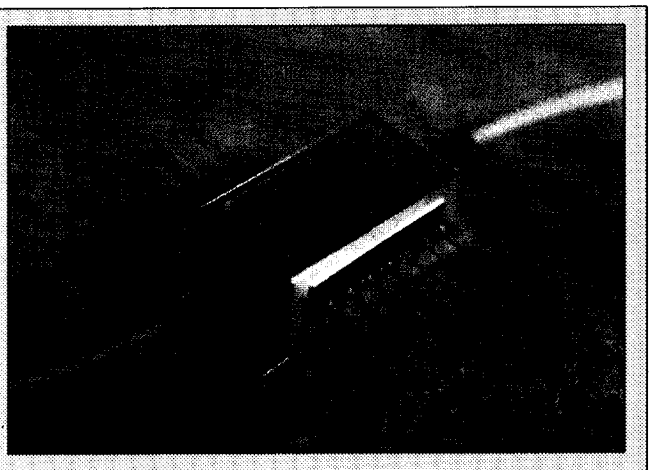

Lasertron's first commercial double-pump semi laser for use in telecoms specifically to pump Er-doped fibre amplifiers for fibre optic phone lines. The double-pump package includes two IBM E2 980 nm 70 mW with individual fibre pigtails saves space and has one thermo-electric cooler allowing operation over 140 mW from a single package.

QED SBIR for PDs

After its success with a Phase I contract, Quantum Epitaxial Designs (QED) Bethlehem, PA, USA, has been awarded a USAF Phase II SBIR contract to continue development of advanced photoreceiver materials. It will investigate the basic material problems associated with producing metal-semiconductor - metal (MSM) photodetector (PD) structures on top of HEMT structures for OEIC device fabrication.

"The 2-year contract will concentrate solely on the optimization of 76 mm, InGaAs / InAlAs / InP OEIC structures grown in-house by solid source MBE," says Will Weisbecker, QED's Technical Director.

"This work will greatly complement our existing production of lattice-matched HEMT epiwafers which have been part of our merchant epiwafer business for some years now. It will be a useful complement to our QW IR photodetector materials and wide range InP- and GaAs-based epiwafers."

Hughes Astra GaAs PVs

In an agreement with SES of Luxembourg Hughes Aircraft Co. is to build the seventh Astra satellite with an option for an eight bringing the total number built by Hughes for SES to five.

Called Astra 1G, it is Hughes most powerful spacecraft design to date. Based on the successful HS 601 body-stabilized bus, it will use new solar panels using GaAs for the first time, these will boost the satellite's generating power to 8 kW allowing SES to extend the Astra system's TV and radio coverage to more of Europe. The contract calls for 15 years of operation.

■ *Contact: Hughes Space & communications Co., PO Box 92919 (S10/S323) Los Angeles, CA 90009 USA. Tel: [1] (310) 364 6363.*

Harris power diodes match GaAs

A new group of diodes featuring the "industry's fastest recovery specs to minimize noise and losses" in high-frequency power switching circuits is available from Harris Semiconductor.

Beyond outperforming all silicon competitors, the Hyperfast diode's speed rivals experimental GaAs diodes announced by Motorola.

Reports have speculated about the future availability of an experimental 600-V, 3-A GaAs Schottky diode with 10 ns t_{rr} – for $4.00, once the part yields. "So for five times the price of the Harris Hyperfast parts, the designer gains a few seconds (scaling for twice the current)", says Harris.

Anadigics 10th Birthday

Warren, NJ, based Anadigics Inc. recently celebrated its tenth year of operation. Anadigics has grown to be possibly the world's most capable merchant manufacturer of high frequency GaAs ICs, numbering amongst its markets telecom and consumer electronic applications such as DBS, cable TV set top receivers, cellular phones, fibre optic comms and wireless computer applications.

In its ninth year Anadigics became the first independent manufacturer of GaAs ICs to receive ISO 9001 certification and has won many awards for its entrepreneurial style of business.

Vitesse SONET/ATM

Camarillo-based, Vitesse Semiconductor Corp., has introduced what it describes as "the industry's lowest cost, lowest power 622 Mb/s SONET/ATM transceiver"; it combines serialization and de-serialization functions with a fully monolithic clock multiplier on a single IC.

The VSC8110 is said to set a new industry price point of one-half to one-third the cost of competing solutions, Vitesse claims. It is derived from a mature ASIC currently in production for a "major telecom equipment manufacturer". Its proven reliability and no off-board components should make it a popular component Vitesse hopes.

Vitesse is working closely with PMC-Sierra and Hewlett-Packard to develop a complete solution for customers' ATM applications. In combination with these companies' products it provides the lowest-cost and lowest-power answer to implementing ATM interfaces for both single-mode and multi-mode fibre applications, it says.

The chip is packaged in a 100QFP with integrated heat spreader and dissipates < 2 W worst case. Manufactured using Vitesse's mature H-GaAs III 0.6μm process, sample quantities will be available in April with production in May and pricing is $52 in 1k quantities.